

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSII·5)

2SK1119

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS
DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS
Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)}=3.0\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}|=2.0S$ (Typ.)
- Low Leakage Current : $I_{DSS}=300\mu A$ (Max.) ($V_{DS}=800V$)
- Enhancement-Mode : $V_{th}=1.5\sim 3.5V$ ($V_{DS}=10V$, $I_D=1mA$)

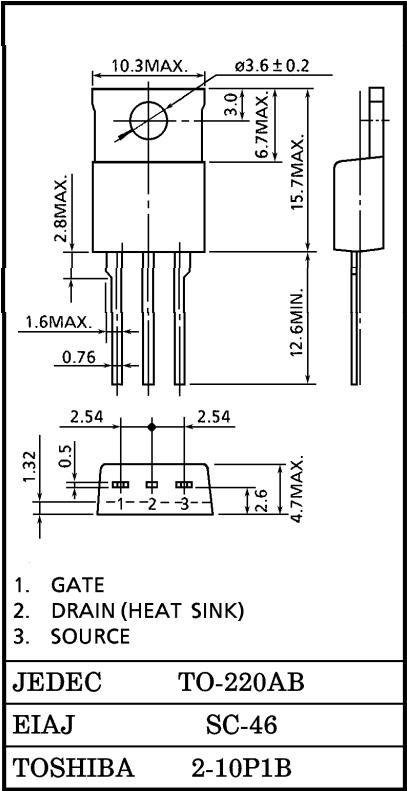
MAXIMUM RATINGS ($T_a=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	1000	V
Drain-Gate Voltage ($R_{GS}=20k\Omega$)	V_{DGR}	1000	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC	I_D	A
	Pulse	I_{DP}	
Drain Power Dissipation ($T_c=25^{\circ}C$)	P_D	100	W
Channel Temperature	T_{ch}	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	$-55\sim 150$	$^{\circ}C$

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	1.25	$^{\circ}C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	83.3	$^{\circ}C/W$

This transistor is an electrostatic sensitive device.
Please handle with caution.

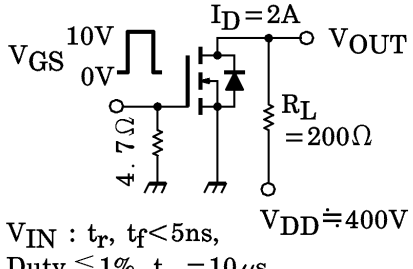


Weight : 2.0g (Typ.)

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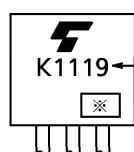
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	—	—	± 100	nA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 800V, V_{GS} = 0V$	—	—	300	μA
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = 10mA, V_{GS} = 0V$	1000	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10V, I_D = 1mA$	1.5	—	3.5	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 2A$	—	3.0	3.8	Ω
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 20V, I_D = 2A$	1.0	2.0	—	S
Input Capacitance		C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	—	700	—	pF
Reverse Transfer Capacitance		C_{rss}		—	55	—	
Output Capacitance		C_{oss}		—	100	—	
Switching Time	Rise Time	t_r	 $V_{IN} : t_r, t_f < 5ns,$ $Duty \leq 1\%, t_W = 10\mu s$	—	18	—	ns
	Turn-on Time	t_{on}		—	30	—	
	Fall Time	t_f		—	12	—	
	Turn-off Time	t_{off}		—	70	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} = 400V, V_{GS} = 10V, I_D = 6A$	—	60	—	nC
Gate-Source Charge		Q_{gs}		—	35	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	25	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	4	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	12	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 4A, V_{GS} = 0V$	—	—	-1.9	V

MARKING



TYPE

※ Lot Number



Month (Starting from Alphabet A)

Year (Last Number of the Christian Era)

